MBR2080CTG, MBR2090CTG, **MBR20100CTG**

Switch-mode **Power Rectifiers**

This series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Shipped 50 units per plastic tube
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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MARKING DIAGRAM



- = Assembly Location A Υ
 - = Year

х

- WW = Work Week B20x0 = Device Code
 - = 8, 9 or 10
 - = Pb-Free Device
- G = Polarity Designator AKA

ORDERING INFORMATION

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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MAXIMUM RATINGS (Per Diode Leg)

		MBR			
Rating	Symbol	2080CT	2090CT	20100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	80	90	100	V
Average Rectified Forward Current (Rated V_R) T _C = 133°C	I _{F(AV)}		10		A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 133°C	I _{FRM}	20		A	
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150 A		A	
Peak Repetitive Reverse Surge Current (2.0 µs, 1.0 kHz)	I _{RRM}		0.5		А
Operating Junction Temperature (Note 1)	TJ		-65 to +17	5	°C
Storage Temperature	T _{stg}		-65 to +17	5	°C
Voltage Rate of Change (Rated V _R)	dv/dt		10,000		V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case	$R_{ heta JC}$	2.0	°C/W
Junction-to-Ambient	$R_{ heta JA}$	60	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
	VF	0.75 0.85 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}C$) (Rated dc Voltage, $T_C = 25^{\circ}C$)	i _R	6.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping
MBR2080CTG	TO–220 (Pb–Free)	50 Units / Rail
MBR2090CTG	TO–220 (Pb–Free)	50 Units / Rail
MBR20100CTG	TO-220 (Pb-Free)	50 Units / Rail

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Figure 2. Typical Reverse Current Per Diode



Figure 3. Typical Current Derating, Case, Per Leg

Figure 4. Typical Current Derating, Ambient, Per Leg





MBR2080CTG, MBR2090CTG, MBR20100CTG

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

2.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Ζ		0.080		2.04	

STYLE 6: PIN 1. ANODE 2. CATHODE ANODE 3. CATHODE

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